Armin Dadgar

List of Publications by Year
in descending order

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250	7,565	50276	64796
papers	citations	46 h-index	79 g-index

259	259	259	5459
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Highly reflective and conductive AlInN/GaN distributed Bragg reflectors realized by Ge-doping. Japanese Journal of Applied Physics, 2022, 61, 015501.	1.5	0
2	Desorption induced formation of low-density GaN quantum dots: nanoscale correlation of structural and optical properties. Journal Physics D: Applied Physics, 2022, 55, 145102.	2.8	0
3	Defect characterization of heavy-ion irradiated AlInN/GaN on Si high-electron-mobility transistors. Journal Physics D: Applied Physics, 2022, 55, 115107.	2.8	1
4	Understanding High-Energy 75-MeV Sulfur-Ion Irradiation-Induced Degradation in GaN-Based Heterostructures: The Role of the GaN Channel Layer. IEEE Transactions on Electron Devices, 2021, 68, 24-28.	3.0	5
5	Raman tensor determination of transparent uniaxial crystals and their thin filmsâ€”a-plane GaN as exemplary case. Applied Physics Letters, 2021, 119, 121109.	3.3	0
6	Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. Journal of Crystal Growth, 2021, 571, 126250.	1.5	6
7	Low-resistivity vertical current transport across AlInN/GaN interfaces. Japanese Journal of Applied Physics, 2021, 60, 010905.	1.5	1
8	Reliable GaN-Based THz Gunn Diodes With Side-Contact and Field-Plate Technologies. IEEE Access, 2020, 8, 84116-84122.	4.2	19
9	The impurity size-effect and phonon deformation potentials in wurtzite GaN. Semiconductor Science and Technology, 2020, 35, 095033.	2.0	4
10	Nitride Microcavities and Single Quantum Dots for Classical and Non-classical Light Emitters. Springer Series in Solid-state Sciences, 2020, , 453-504.	0.3	1
11	Fabrication and characterization of high power Gallium Nitride based terahertz Gunn diodes. , 2020, , .		0
12	Methodology for the investigation of threading dislocations as a source of vertical leakage in AlGaN/GaN-HEMT heterostructures for power devices. Journal of Applied Physics, 2019, 125, .	2.5	30
13	Outstanding Reliability of Heavy-Ion-Irradiated AlInN/GaN on Silicon HFETs. IEEE Transactions on Nuclear Science, 2019, 66, 2417-2421.	2.0	4
14	Impact of AlN/Si Nucleation Layers Grown Either by NH₃â€MBE or MOCVD on the Properties of AlGaN/GaN HFETs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700638.	1.8	0
15	Flexible Modulation of Electronic Band Structures of Wide Band Gap GaN Semiconductors Using Bioinspired, Nonbiological Helical Peptides. Advanced Functional Materials, 2018, 28, 1704034.	14.9	9
16	Two charge states of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">C</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:msub></mml:math> acceptor in GaN: Evidence from photoluminescence. Physical Review B, 2018, 98, .	3.2	84
17	Accurate determination of polarization fields in (0â€‰0â€‰0â€‰1) c-plane InAlN/GaN heterostructures with capacitance-voltage-measurements. Journal Physics D: Applied Physics, 2018, 51, 485103.	2.8	5
18	Valence band tomography of wurtzite GaN by spectroscopic ellipsometry. Applied Physics Express, 2018, 11, 101001.	2.4	10

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19	Electronic excitations stabilized by a degenerate electron gas in semiconductors. Communications Physics, 2018, 1, .	5.3	6
20	Gallium nitride vertical power devices on foreign substrates: a review and outlook. Journal Physics D: Applied Physics, 2018, 51, 273001.	2.8	173
21	LED Materials: GaN on Si. , 2017, , 123-147.		1
22	Radiation-induced alloy rearrangement in InxGa1â^'xN. Applied Physics Letters, 2017, 110, .	3.3	11
23	All metalorganic chemical vapor phase epitaxy of p/n-GaN tunnel junction for blue light emitting diode applications. Applied Physics Letters, 2017, 110, .	3.3	59
24	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, .	3.3	6
25	Properties of Câ€doped GaN. Physica Status Solidi (B): Basic Research, 2017, 254, 1600708.	1.5	33
26	High-Performance 500 V Quasi- and Fully-Vertical GaN-on-Si pn Diodes. IEEE Electron Device Letters, 2017, 38, 248-251.	3.9	70
27	Breakdown of Far-Field Raman Selection Rules by Lightâ€“Plasmon Coupling Demonstrated by Tip-Enhanced Raman Scattering. Journal of Physical Chemistry Letters, 2017, 8, 5462-5471.	4.6	16
28	Reduction of on-resistance and current crowding in quasi-vertical GaN power diodes. Applied Physics Letters, 2017, 111, .	3.3	39
29	Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, .	2.5	23
30	Unintentional indium incorporation into barriers of InGaN/GaN multiple quantum wells studied by photoreflectance and photoluminescence excitation spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	5
31	On reduction of current leakage in GaN by carbon-doping. Applied Physics Letters, 2016, 109, .	3.3	25
32	Polarization engineering of câ€plane InGaN quantum wells by pulsedâ€flow growth of AlInGaN barriers. Physica Status Solidi (B): Basic Research, 2016, 253, 118-125.	1.5	6
33	Nanoscale cathodoluminescence of stacking faults and partial dislocations in aâ€plane GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 73-77.	1.5	2
34	Termination of hollow core nanopipes in GaN by an AlN interlayer. Journal of Crystal Growth, 2016, 455, 43-48.	1.5	5
35	Clustered quantum dots in single GaN islands formed at threading dislocations. Japanese Journal of Applied Physics, 2016, 55, 05FF04.	1.5	5
36	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	1.5	11

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37	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, .	3.3	29
38	Enhanced sheet carrier densities in polarization controlled AlInN/AlN/GaN/InGaN field-effect transistor on Si (111). AIP Advances, 2015, 5, .	1.3	4
39	Germanium - the superior dopant in n-type GaN. Physica Status Solidi - Rapid Research Letters, 2015, 9, 716-721.	2.4	40
40	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.	1.5	22
41	Sixteen years GaN on Si. Physica Status Solidi (B): Basic Research, 2015, 252, 1063-1068.	1.5	76
42	Growth of III/Vs on Silicon. , 2015, , 1249-1300.		8
43	LED Materials: GaN on Si. , 2015, , 1-21.		1
44	High-frequency detection of cell activity ofPhysarum polycephalumby a planar open gate AlGaN/GaN HEMT. Journal Physics D: Applied Physics, 2014, 47, 425401.	2.8	4
45	High-pressure Raman scattering in InGaN heteroepitaxial layers: Effect of the substrate on the phonon pressure coefficients. Applied Physics Letters, 2014, 104, 142101.	3.3	2
46	Wafer curvature, temperature inhomogeneity, plastic deformation and their impact on the properties of GaN on silicon power and optoâ€electronic structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 397-400.	0.8	6
47	Band gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mrow><mml:mn>10</mml:mn></mml:mrow><mml:mn>20</mml:mn></mml:msup><mml:mtext>cm</mml:mtext><mml:mrow><mml:mo>â^’</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:math>. Physical Review B, 2014, 90, .	3.2	133
48	Characterization of AlInN/AlN/GaN FET structures using x-ray diffraction, x-ray reflectometry and grazing incidence x-ray fluorescence analysis. Journal Physics D: Applied Physics, 2014, 47, 355106.	2.8	6
49	Anisotropic bow and plastic deformation of GaN on silicon. Journal of Crystal Growth, 2013, 370, 278-281.	1.5	14
50	16th International Conference on Metalorganic Vapor Phase Epitaxy. Journal of Crystal Growth, 2013, 370, 1.	1.5	0
51	Green to blue polarization compensated c-axis oriented multi-quantum wells by AlGaInN barrier layers. Applied Physics Letters, 2013, 102, .	3.3	13
52	In-situ growth monitoring of AlInN/AlGaN distributed Bragg reflectors for the UV-spectral range. Journal of Crystal Growth, 2013, 370, 87-91.	1.5	18
53	MOVPE growth of semi-polar GaN light-emitting diode structures on planar Si(112) and Si(113) substrates. Journal of Crystal Growth, 2013, 370, 288-292.	1.5	15
54	Growth and characterization of stacking fault reduced GaN $(1,0,ar{1},3)$ on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308.	2.8	12

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55	Anisotropy of effective electron masses in highly doped nonpolar GaN. Applied Physics Letters, 2013, 103, .	3.3	33
56	Ge as a surfactant in metal-organic vapor phase epitaxy growth of a-plane GaN exceeding carrier concentrations of 1020Âcmâ^3. Applied Physics Letters, 2013, 103, .	3.3	18
57	Systematic Optical Characterization of Two-Dimensional Electron Gases in InAlN/GaN-Based Heterostructures with Different In Content. Japanese Journal of Applied Physics, 2013, 52, 08JK02.	1.5	1
58	Optical characterization of a InGaN/GaN microcavity with epitaxial AlInN/GaN bottom DBR. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
59	High Si and Ge n-type doping of GaN doping - Limits and impact on stress. Applied Physics Letters, 2012, 100, .	3.3	160
60	Luminescence from two-dimensional electron gases in InAlN/GaN heterostructures with different In content. Applied Physics Letters, 2012, 100, .	3.3	12
61	Thermally Oxidized InAlN of Different Compositions for InAlN/GaN Heterostructure Field-Effect Transistors. Journal of Electronic Materials, 2012, 41, 3013-3016.	2.2	4
62	Cathodoluminescence directly performed in a transmission electron microscope: nanoscale correlation of structural and optical properties. Microscopy and Microanalysis, 2012, 18, 1834-1835.	0.4	1
63	Role of low-temperature AlGaN interlayers in thick GaN on silicon by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	2.5	36
64	Optical anisotropy of aâ€plane Al_{0.8}In_{0.2}N grown on an aâ€plane GaN pseudosubstrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 29-32.	1.8	0
65	Growth of AlInN/AlGaN distributed Bragg reflectors for high quality microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1253-1258.	0.8	11
66	Growth and stacking fault reduction in semiâ€polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510.	0.8	16
67	Al_xGa_{1â^'x}N/GaN heterostructures on a thin silicon-on-insulator substrate for metalâ€“semiconductorâ€“metal photodetectors. Journal Physics D: Applied Physics, 2011, 44, 365102.	2.8	6
68	Influence of exciton-phonon coupling and strain on the anisotropic optical response of wurtzite AlN around the band edge. Physical Review B, 2011, 83, .	3.2	46
69	Stranskiâ€“Krastanov transition and self-organized structures in low-strained AlInN/GaN multilayer structures. Semiconductor Science and Technology, 2011, 26, 014041.	2.0	5
70	Comment on â€œThe effects of Si doping on dislocation movement and tensile stress in GaN filmsâ€•[J. Appl. Phys. 109, 073509 (2011)]. Journal of Applied Physics, 2011, 110, 096101.	2.5	3
71	Electrical investigations of AlGaN/AlN structures for LEDs on Si(111). Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1597-1599.	1.8	9
72	Impact of AlN seeding layer growth rate in MOVPE growth of semiâ€polar gallium nitride structures on high index silicon. Physica Status Solidi (B): Basic Research, 2011, 248, 594-599.	1.5	6

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73	Heavy Si doping: The key in heteroepitaxial growth of aâ€plane GaN without basal plane stacking faults?. Physica Status Solidi (B): Basic Research, 2011, 248, 578-582.	1.5	17
74	Characterization of AlGaInN layers using Xâ€ray diffraction and fluorescence. Physica Status Solidi (B): Basic Research, 2011, 248, 622-626.	1.5	6
75	Improving GaNâ€onâ€silicon properties for GaN device epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1503-1508.	0.8	59
76	Optical investigation of a hybrid GaN based microcavity with AlInN/GaN bottom and dielectric top distributed Bragg mirror. Superlattices and Microstructures, 2011, 49, 187-192.	3.1	3
77	Unintentional doping ofa-plane GaN by insertion ofin situSiN masks. Journal Physics D: Applied Physics, 2011, 44, 085102.	2.8	1
78	Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905.	3.3	22
79	Crack-Free, Highly Conducting GaN Layers on Si Substrates by Ge Doping. Applied Physics Express, 2011, 4, 011001.	2.4	73
80	Thin-film InGaNâ•GaN Vertical Light Emitting Diodes Using GaN on Silicon-On-Insulator Substrates. Electrochemical and Solid-State Letters, 2011, 14, H460.	2.2	15
81	Stress Relaxation in Low-Strain AlInN/GaN Bragg Mirrors. Japanese Journal of Applied Physics, 2011, 50, 031002.	1.5	0
82	Stress Relaxation in Low-Strain AlInN/GaN Bragg Mirrors. Japanese Journal of Applied Physics, 2011, 50, 031002.	1.5	1
83	Metalorganic vapor-phase epitaxy of GaN layers on Si substrates with Si(110) and other high-index surfaces. Journal of Crystal Growth, 2010, 312, 180-184.	1.5	17
84	Strain profiling of AlInN/GaN distributed Bragg reflectors using in situ curvature measurements and ex situ X-ray diffraction. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2010, 528, 58-64.	5.6	8
85	Monitoring glycolytic oscillations using AlGaN/GaN high electron mobility transistors (HEMTs). Sensors and Actuators B: Chemical, 2010, 149, 310-313.	7.8	6
86	Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682.	1.5	26
87	Impedance spectroscopy of AlGaN/GaN HEMTs in contact with culture media. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 464-467.	0.8	4
88	Light extraction from GaNâ€based LED structures on siliconâ€onâ€insulator substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 88-91.	0.8	6
89	GaN LEDs on silicon. , 2010, , .		0
90	Luminescence Properties of Photonic Crystal InGaN/GaN Light Emitting Layers on Silicon-on-Insulator. Electrochemical and Solid-State Letters, 2010, 13, H343.	2.2	6

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91	Direct microscopic correlation of crystal orientation and luminescence in spontaneously formed nonpolar and semipolar GaN growth domains. Applied Physics Letters, 2010, 96, .	3.3	6
92	Semipolar single component GaN on planar high index Si(11h) substrates. Applied Physics Letters, 2010, 97, .	3.3	22
93	Strain evaluation in AlInN/GaN Bragg mirrors by in situ curvature measurements and ex situ x-ray grazing incidence and transmission scattering. Applied Physics Letters, 2010, 97, .	3.3	21
94	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. Applied Physics Letters, 2010, 97, 173505.	3.3	19
95	Microstructure of gallium nitride films grown on silicon (110). Applied Physics Letters, 2010, 96, 231908.	3.3	12
96	X-ray Study of Step Induced Lateral Correlation Lengths in Thin AlGaN Nucleation Layers. Japanese Journal of Applied Physics, 2010, 49, 025503.	1.5	0
97	Temperature rise in InGaN/GaN vertical light emitting diode on copper transferred from silicon probed by Raman scattering. Journal of Applied Physics, 2010, 108, .	2.5	16
98	Dielectric function and optical properties of Al-rich AlInN alloys pseudomorphically grown on GaN. Journal Physics D: Applied Physics, 2010, 43, 365102.	2.8	66
99	Metal organic vapor phase epitaxy growth of single crystalline GaN on planar Si(211) substrates. Applied Physics Letters, 2009, 95, .	3.3	27
100	Photoelectric properties of the undoped GaN/AlN interlayer/high purity Si(1â€‰1â€‰1) interface. Journal Physics D: Applied Physics, 2009, 42, 205103.	2.8	4
101	InGaN/GaN light-emitting diodes on Si(1â€‰1â€‰0) substrates grown by metalâ€“organic vapour phase epitaxy. Journal Physics D: Applied Physics, 2009, 42, 055107.	2.8	35
102	GaNâ€based deep green light emitting diodes on siliconâ€onâ€insulator substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S822.	0.8	3
103	AlInN/GaN based multi quantum well structures â€“ growth and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S451.	0.8	11
104	MOVPE growth of highâ€quality Al_{0.1}Ga_{0.9}N on Si(111) substrates for UVâ€LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S455.	0.8	3
105	Microâ€structural anisotropy of aâ€plane GaN analyzed by high resolution Xâ€ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498.	0.8	12
106	Effect of growth conditions on vacancy defects in MOVPE grown AlN thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2575-2577.	0.8	4
107	Characterization of defects in undoped non c-plane and high resistance GaN layers dominated by stacking faults. Physica B: Condensed Matter, 2009, 404, 4922-4924.	2.7	7
108	Influence of anisotropic strain on excitonic transitions in a-plane GaN films. Microelectronics Journal, 2009, 40, 322-324.	2.0	10

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109	Low-temperature/high-temperature AlN superlattice buffer layers for high-quality AlxGa1â^'xN on Si (111). Journal of Crystal Growth, 2009, 311, 3742-3748.	1.5	20
110	Cathodoluminescence of epitaxial GaN and ZnO thin films for scintillator applications. Journal of Crystal Growth, 2009, 311, 3984-3988.	1.5	12
111	Fabrication, Self-Assembly, and Properties of Ultrathin AlN/GaN Porous Crystalline Nanomembranes: Tubes, Spirals, and Curved Sheets. ACS Nano, 2009, 3, 1663-1668.	14.6	91
112	Analysis of point defects in AlN epilayers by cathodoluminescence spectroscopy. Applied Physics Letters, 2009, 95, .	3.3	28
113	Electron-beam processed SAW devices for sensor applications. , 2009, , .		1
114	High-overtone bulk acoustic wave resonator on galliumnitride. , 2009, , .		0
115	GaN growth on silane exposed AlN seed layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1675-1677.	0.8	2
116	MOVPE growth of blue In_xGa_{1â€“x}N/GaN LEDs on 150 mm Si(001). Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2238-2240.	0.8	5
117	Investigations of a-plane and c-plane GaN-based Synchronous Surface Acoustic Wave Resonators. , 2008, , .		3
118	MOVPE Growth and Characterization of AlInN FET Structures on Si(111). Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	10
119	Two-dimensional electron gas based actuation of piezoelectric AlGaN/GaN microelectromechanical resonators. Applied Physics Letters, 2008, 93, .	3.3	36
120	GaN-based microdisk light emitting diodes on (111)-oriented nanosilicon-on-insulator templates. Journal of Applied Physics, 2008, 104, 053106.	2.5	5
121	a-plane GaN Shear Wave Thin Film Resonator. Frequency Control Symposium and Exhibition, Proceedings of the IEEE International, 2007, , .	0.0	2
122	In Ga N â^• Ga N light emitting diodes on nanoscale silicon on insulator. Applied Physics Letters, 2007, 91, .	3.3	34
123	Metal-organic vapor phase epitaxy and properties of AlInN in the whole compositional range. Applied Physics Letters, 2007, 90, 022105.	3.3	119
124	Thermal stability of metal organic vapor phase epitaxy grown AlInN. Applied Physics Letters, 2007, 90, 221906.	3.3	53
125	Electrical characterization of defect states in local conductivity domains in ZnO:N,As layers. Journal of Materials Research, 2007, 22, 1775-1778.	2.6	4
126	Metalorganic vapor phase epitaxy of ZnO: towards p-type conductivity. , 2007, 6474, 32.		9

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127	Epitaxy of GaN on siliconâ€"impact of symmetry and surface reconstruction. New Journal of Physics, 2007, 9, 389-389.	2.9	124
128	Fabry-Perot effects in InGaNâˆ•GaN heterostructures on Si-substrate. Journal of Applied Physics, 2007, 101, 033113.	2.5	69
129	Complex excitonic recombination kinetics in ZnO: Capture, relaxation, and recombination from steady state. Applied Physics Letters, 2007, 90, 041917.	3.3	31
130	MOVPE growth of GaN on Si â€“ Substrates and strain. Thin Solid Films, 2007, 515, 4356-4361.	1.8	81
131	Crystallographic and electric properties of MOVPE-grown AlGaN/GaN-based FETs on Si(001) substrates. Journal of Crystal Growth, 2007, 299, 399-403.	1.5	12
132	Homoepitaxial growth of ZnO by metalorganic vapor phase epitaxy in two-dimensional growth mode. Journal of Crystal Growth, 2007, 308, 170-175.	1.5	37
133	Blue light emitting diodes on Si(001) grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 41-44.	0.8	4
134	Laser-Interference Lithography Tailored for Highly Symmetrically Arranged ZnO Nanowire Arrays. Small, 2007, 3, 76-80.	10.0	95
135	Modulation spectroscopy of AlGaN/GaN heterostructures: The influence of electron-hole interaction. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 447-458.	1.8	23
136	Influence of excitons and electric fields on the dielectric function of GaN: Theory and experiment. Physical Review B, 2006, 74, .	3.2	22
137	Optical and structural microanalysis of GaN grown on SiN submonolayers. Journal of Applied Physics, 2006, 99, 123518.	2.5	33
138	Piezoelectric GaN sensor structures. IEEE Electron Device Letters, 2006, 27, 309-312.	3.9	113
139	Metalorganic vapor phase epitaxy grown InGaNâˆ•GaN light-emitting diodes on Si(001) substrate. Applied Physics Letters, 2006, 88, 121114.	3.3	42
140	Template-Assisted Large-Scale Ordered Arrays of ZnO Pillars for Optical and Piezoelectric Applications. Small, 2006, 2, 561-568.	10.0	209
141	Local p-type conductivity in n-GaN and n-ZnO layers due to inhomogeneous dopant incorporation. Physica B: Condensed Matter, 2006, 376-377, 703-706.	2.7	11
142	Well-ordered ZnO nanowire arrays on GaN substrate fabricated via nanosphere lithography. Journal of Crystal Growth, 2006, 287, 34-38.	1.5	108
143	Avoidance of surface-related defects in MOVPE-grown InGaP layers. Journal of Crystal Growth, 2006, 287, 633-636.	1.5	1
144	Growth of single-domain GaN layers on Si(001) by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2006, 289, 485-488.	1.5	33

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145	Growth of blue GaN LED structures on 150-mm Si(111). Journal of Crystal Growth, 2006, 297, 279-282.	1.5	117
146	MOVPE growth of high-quality AlN. Journal of Crystal Growth, 2006, 297, 306-310.	1.5	68
147	GaN micromachined FBAR structures for microwave applications. Superlattices and Microstructures, 2006, 40, 426-431.	3.1	24
148	Metalorganic chemical vapor phase epitaxy and structural properties of Ga1-xPxN on GaN/Si(111) substrates. Applied Physics A: Materials Science and Processing, 2006, 82, 733-735.	2.3	4
149	Electric-Field-Enhanced Thermal Emission from Osmium-Related Deep Level in n-GaAs. Advances in Science and Technology, 2006, 46, 73.	0.2	0
150	Epitaxy of GaN LEDs on large substrates: Si or sapphire?. , 2006, , .		22
151	Electrical Characterization of Defect States in Local Conductivity Domains in ZnO:N,As Layers. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
152	Electroreflectance spectroscopy of Ptâˆ•AlGaNâˆ•GaN heterostructures exposed to gaseous hydrogen. Applied Physics Letters, 2006, 88, 024101.	3.3	16
153	Vapour-transport-deposition growth of ZnO nanostructures: switch betweenc-axial wires anda-axial belts by indium doping. Nanotechnology, 2006, 17, S231-S239.	2.6	97
154	In situ monitoring of the stress evolution in growing group-III-nitride layers. Journal of Crystal Growth, 2005, 275, 209-216.	1.5	40
155	Transient Thermal Characterization of AlGaN/GaN HEMTs Grown on Silicon. IEEE Transactions on Electron Devices, 2005, 52, 1698-1705.	3.0	78
156	A low-temperature evaporation route for ZnO nanoneedles and nanosaws. Applied Physics A: Materials Science and Processing, 2005, 80, 457-460.	2.3	17
157	ZnO MOVPE growth: From local impurity incorporation towards p-type doping. Superlattices and Microstructures, 2005, 38, 245-255.	3.1	27
158	High-current AlInN/GaN field effect transistors. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 832-836.	1.8	36
159	Simultaneous measurement of wafer curvature and true temperature during metalorganic growth of group-III nitrides on silicon and sapphire. Physica Status Solidi (B): Basic Research, 2005, 242, 2570-2574.	1.5	13
160	Deep levels in Ruthenium doped p-type MOCVD GaAs. AIP Conference Proceedings, 2005, , .	0.4	0
161	Deep levels in osmium doped p-type GaAs grown by metal organic chemical vapor deposition. AIP Conference Proceedings, 2005, , .	0.4	0
162	Heteroepitaxy of GaN on Silicon: In Situ Measurements. Materials Science Forum, 2005, 483-485, 1051-1056.	0.3	1

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163	Correlation between macroscopic transport parameters and microscopic electrical properties in GaN. Journal of Applied Physics, 2005, 97, 043710.	2.5	6
164	Osmium impurity-related deep levels in n-type GaAs. Journal of Applied Physics, 2005, 98, 083709.	2.5	1
165	Microscopic Spatial Distribution of Bound Excitons in High-Quality ZnO. Materials Science Forum, 2005, 483-485, 1065-0.	0.3	0
166	Recording of cell action potentials with AlGaNâˆ•GaN field-effect transistors. Applied Physics Letters, 2005, 86, 033901.	3.3	112
167	Arrays of vertically aligned and hexagonally arranged ZnO nanowires: a new template-directed approach. Nanotechnology, 2005, 16, 913-917.	2.6	147
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